

LSU404 N-CHANNEL JFET



Linear Systems replaces discontinued Siliconix U404 with LSU404

The U404/ LSU404 is a Low Noise, Low Drift, Monolithic Dual N-Channel JFET

The LSU404 is a high-performance monolithic dual JFET featuring extremely low noise, tight offset voltage and low drift over temperature specifications, and is targeted for use in a wide range of precision instrumentation applications. The LSU404 features a 5mV offset and 10-μV/°C drift. The LSU404 is a direct replacement for discontinued Siliconix U404.

The hermetically sealed TO-71 & TO-78 packages are well suited for military applications.

(See Packaging Information).

U404 / LSU404 Applications:

- Wideband Differential Amps
- High-Speed, Temp-Compensated Single-**Ended Input Amps**
- **High-Speed Comparators**
- Impedance Converters and vibrations detectors.

ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

FEATURES							
LOW DRIFT	-	$ V_{GS1-2}/T = 10\mu V/^{\circ}C$ TYP.					
LOW NOISE		$e_n = 6nV/Hz @ 10Hz TYP.$					
LOW PINCE	HOFF	$V_p = 2.5V TYP.$					
ABSOLUTE MAXIMUM RATINGS							
@ 25°C (unless otherwise noted)							
Maximum Temperatures							
Storage Te	mperature		-65°C to +150°C				
Operating	Junction Temperature		+150°C				
Maximum Voltage and Current for Each Transistor – Note 1							
-V _{GSS}	Gate Voltage to Drain or Source		50V				
-V _{DSO}	Drain to Source Voltage		50V				
-I _{G(f)}	Gate Forward Current	10mA					
Maximum Power Dissipation							
Device Dissipation @ Free Air – Total 300mW							

MATCHING CHARACTERISTICS @ 25°C UNLESS OTHERWISE NOTED						
SYMBOL	CHARACTERISTICS	VALUE	UNITS	CONDITIONS		
V _{GS1-2} / T max.	DRIFT VS.	25	μV/°C	V_{DG} =10V, I_{D} =200 μ A		
	TEMPERATURE			T _A =-55°C to +125°C		
V _{GS1-2} max.	OFFSET VOLTAGE	15	mV	V_{DG} =10V, I_{D} =200 μ A		

TYP. CONDITIONS CHARACTERISTICS MIN MAX. UNITS BV_{GSS} I_D=1nA Breakdown Voltage 50 60 $V_{DS} = 0$ Gate-To-Gate Breakdown __ ±50 ٧ BV_{GGO} $I_D = 0$ $I_s = 0$ $I_G = 1nA$ TRANSCONDUCTANCE 2000 Full Conduction 7000 f = 1kHz 10\/ umho $I_D = 200 \mu A$ f = 1kHzTypica<mark>l O</mark>per<mark>at</mark>ion 1000 2000 μmho 15V Mismatch 0.6 3 % $|Y_{FS1-2}/Y_{FS}|$ **DRAIN CURRENT** V_{DG} = 10V10 V_{GS}= 0V **Full Conduction** 0.5 mA Mismatch at Full Conduction 1 $|I_{DSS1-2}/I_{DSS}|$ 5 % **GATE VOLTAGE** Pinchoff voltage $V_{GS}(off)$ or V_{r} -0.5 -2.5 $V_{DS} = 15V$ $I_D = 1nA$ $V_{DS}=15\overline{V}$ $V_{GS}(on)$ **Operating Range** -2.3 ٧ $I_D = 200 \mu A$ **GATE CURRENT** -I_Gmax. Operating -4 -15 pΑ $V_{DG} = 15V I_D = 200 \mu A$ -I_Gmax. High Temperature -10 nΑ $T_A = +125^{\circ}C$ -l_{GSS}max. At Full Conduction 100 рΑ $V_{DS} = 0$ -I_{GSS}max. High Temperature 5 T_A= +125°C 5 5 рΑ $V_{DG} = 15V$ **OUTPUT CONDUCTANCE Full Conduction** V_{DG}= 10V Yoss 20 μmho $V_{GS} = 0V$ $Y_{\underline{OS}}$ Operating 0.2 2 umho $V_{DG} = 15V$ $I_{D} = 500 \mu A$ **COMMON MODE REJECTION** $V_{DS} = 10 \text{ to } 20V$ **CMR** -20 log | V _{GS1-2}/ V _{DS}| 95 dB $I_D = 30 \mu A$ NOISE $V_{DS} = 15V$ $V_{GS} = 0V$ $R_G = 10M$ NF **Figure** 0.5 dB f= 100Hz NBW= 6Hz V_{DS} =15V I_D =200 μ A f=10Hz NBW=1Hz e_n Voltage 20 nV/√Hz

Reverse Transfer Note 1 - These ratings are limiting values above which the serviceability of any semiconductor may be impaired

CAPACITANCE

Input

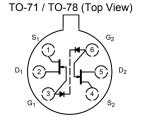
Available Packages:

 $\mathbf{C}_{\underline{\text{ISS}}}$

 C_{RSS}

U404 / LSU404 in TO-71 & TO-78 U404 / LSU404 available as bare die

Please contact Micross for full package and die dimensions



8

1.5

рF

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 $V_{DS} = 15V$ $I_{D} = 200 \mu A$

f= 1MHz